100V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max T_A = +25°C
100V	160mΩ @ V_{GS} = 10V	2.9A
	200mΩ @ V_{GS} = 4.5V	2.6A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Power Management Functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.

Features and Benefits

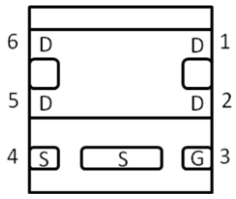
- 0.6mm Profile – Ideal for Low Profile Applications
- PCB Footprint of 4mm^2
- Low On-Resistance
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

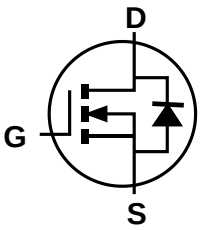
- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e4
- Weight: 0.0065 grams (Approximate)

U-DFN2020-6

Bottom View



Pin Out



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Compliance	Case	Quantity per reel
DMN10H170SFDE-7	Standard	U-DFN2020-6	3,000
DMN10H170SFDE-13	Standard	U-DFN2020-6	10,000

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

U-DFN2020-6

7H = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: B = 2014)
M = Month (ex: 9 = September)

Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020	2020
Code	B	C	D	E	F	G	H	I

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	100	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	2.9 2.3	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	3.4 2.7	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I_{DM}	10	A
Maximum Body Diode Continuous Current			I_S	2.5	A
Avalanche Current (Note 7)			I_{AS}	4.7	A
Avalanche Energy (Note 7)			E_{AS}	16	mJ

Thermal Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	0.66	W
	T_A = +70°C		0.42	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	$R_{\theta JA}$	189	°C/W
	t<10s		132	
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	2.03	W
	T_A = +70°C		1.31	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	$R_{\theta JA}$	61	°C/W
	t<10s		43	
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	9.3	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	100	-	-	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	-	-	1	µA	V_{DS} = 100V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	-	-	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	2.0	3.0	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	-	116	160	mΩ	V_{GS} = 10V, I_D = 5.0A
			126	200		V_{GS} = 4.5V, I_D =5.0A
Diode Forward Voltage	V_{SD}	-	0.9	1.0	V	V_{GS} = 0V, I_S = 10A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	-	1167	-	pF	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	-	36	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	25	-	pF	
Gate Resistance	R_g	-	1.3	-	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	-	4.9	-	nC	V_{DS} = 80V, I_D = 12.8A
Total Gate Charge (V_{GS} = 10V)	Q_g	-	9.7	-	nC	
Gate-Source Charge	Q_{gs}	-	2.0	-	nC	
Gate-Drain Charge	Q_{gd}	-	2.0	-	nC	
Turn-On Delay Time	$t_{D(on)}$	-	10.5	-	ns	V_{DS} = 50V, I_D = 12.8A V_{GS} = 10V, R_G = 25Ω
Turn-On Rise Time	t_r	-	11.1	-	ns	
Turn-Off Delay Time	$t_{D(off)}$	-	42.6	-	ns	
Turn-Off Fall Time	t_f	-	12.8	-	ns	
Reverse Recovery Time	T_{rr}	-	30.3	-	ns	I_F = 12.8A, di/dt = 100A/µs
Reverse Recovery Charge	Q_{rr}	-	35.2	-	nC	

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7 .UIS in production with L = 1.43mH, TJ = +25°C.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

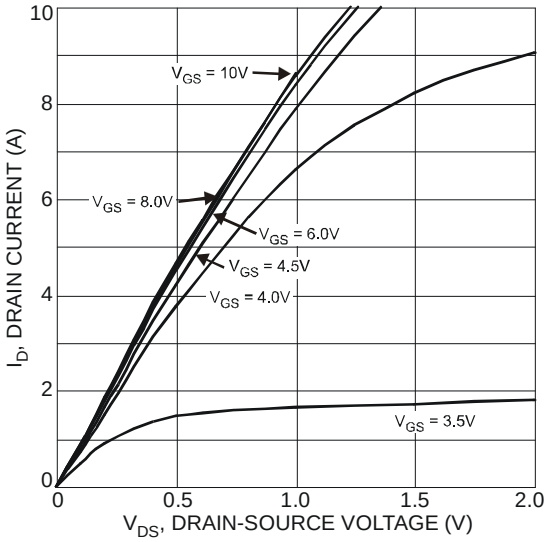


Fig.1 Typical Output Characteristic

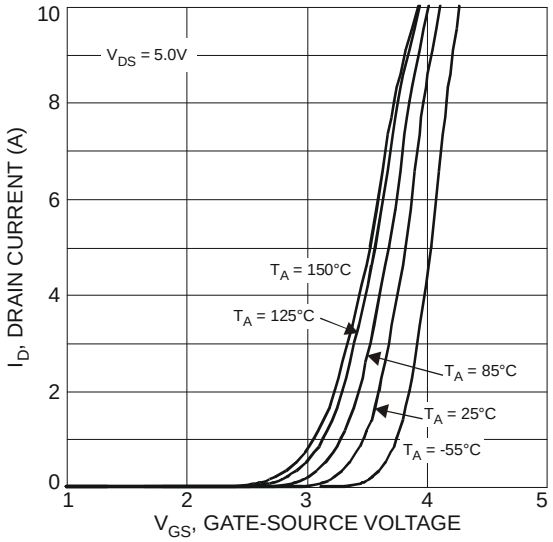


Fig. 2 Typical Transfer Characteristics

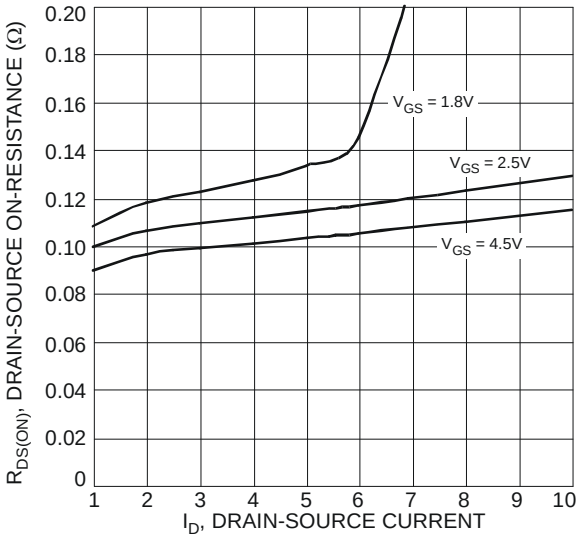


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

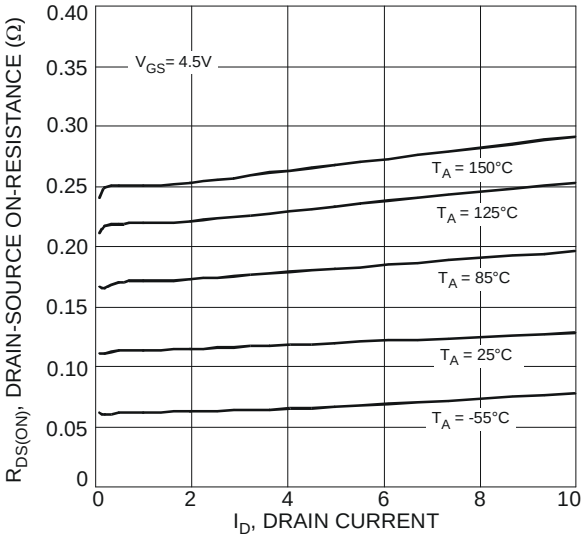


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

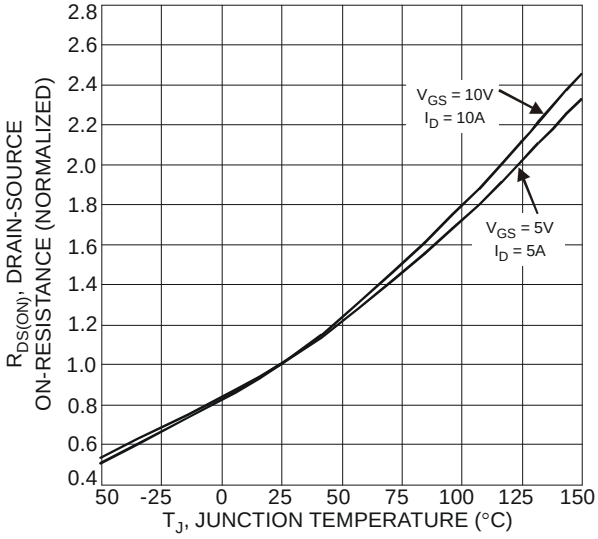


Fig. 5 On-Resistance Variation with Temperature

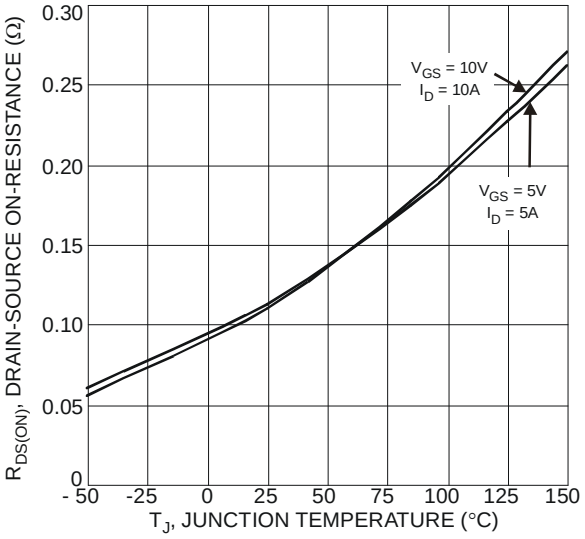


Fig. 6 On-Resistance Variation with Temperature

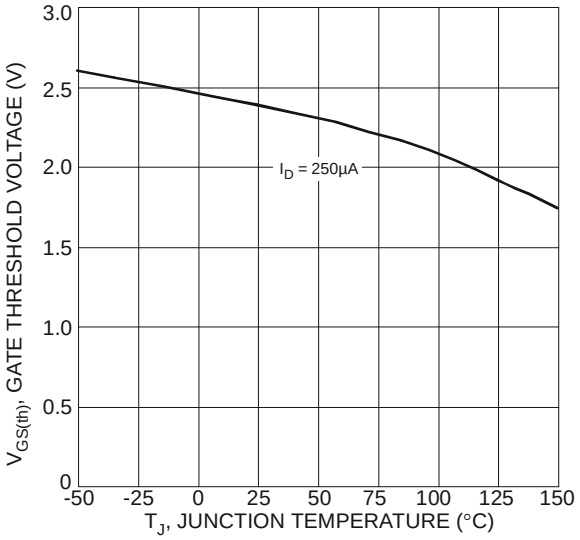


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

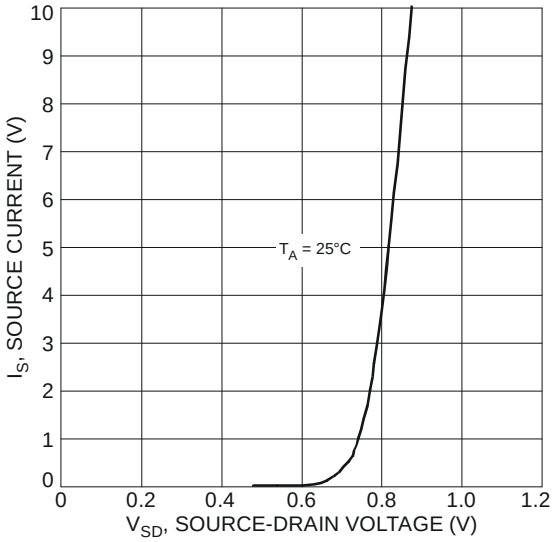


Fig. 8 Diode Forward Voltage vs. Current

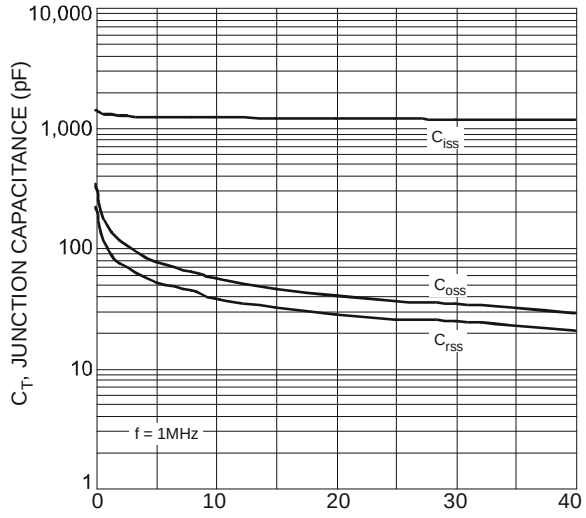


Fig. 9 Typical Junction Capacitance

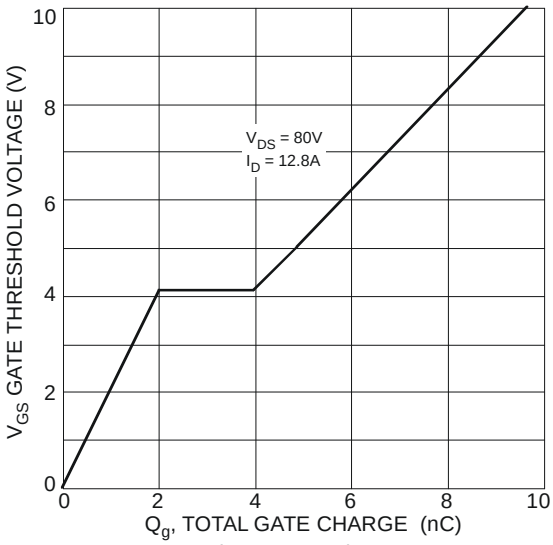


Fig. 10 Gate Charge

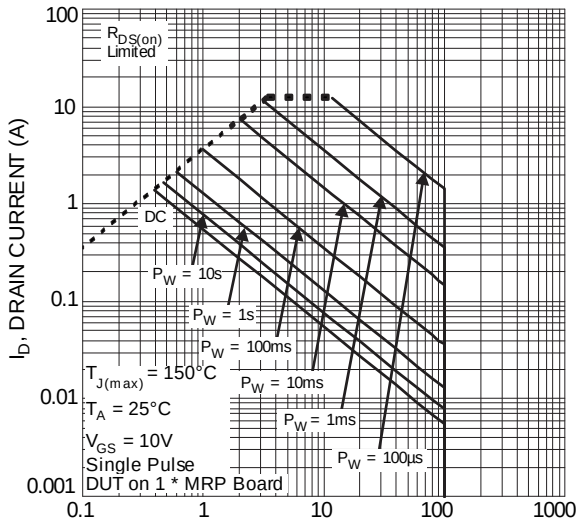


Figure 11 SOA, Safe Operation Area

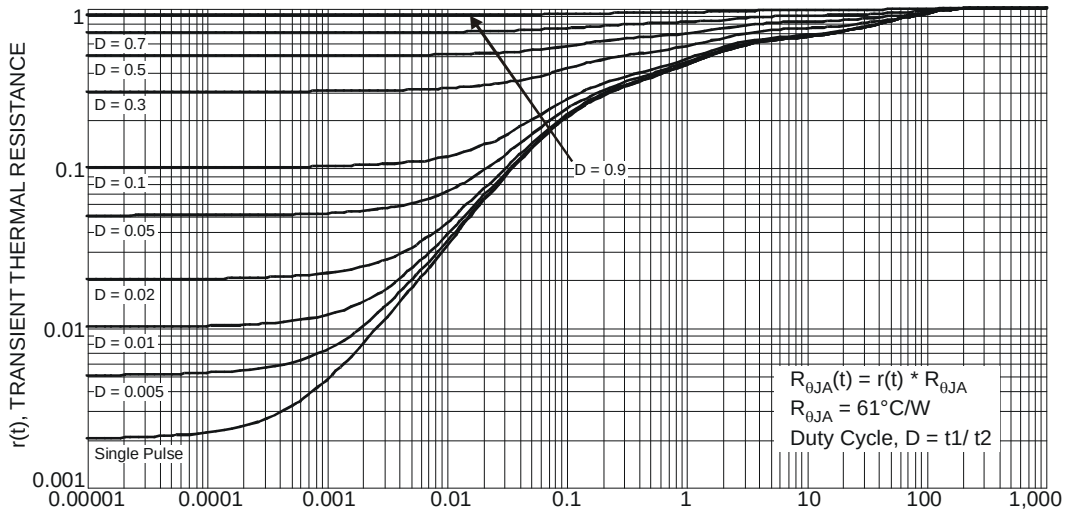
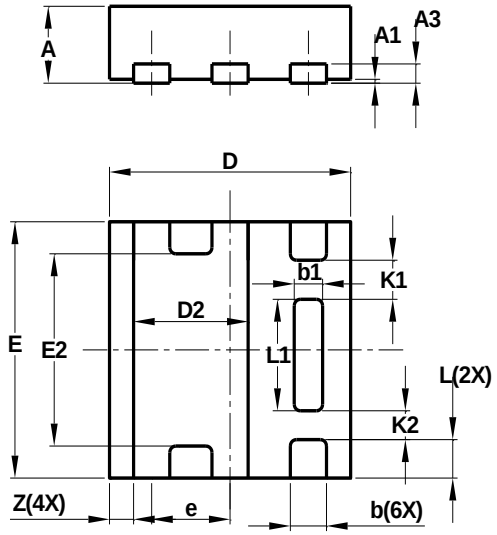


Figure 12 Transient Thermal Resistance

Package Outline Dimensions

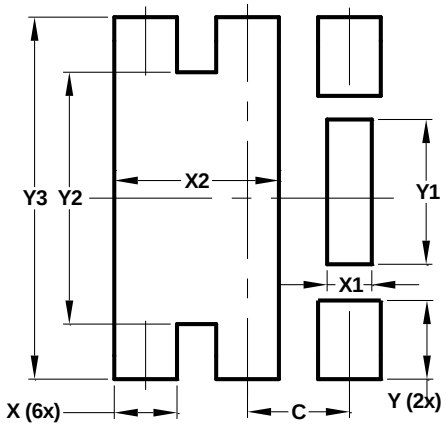
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



U-DFN2020-6 Type E			
Dim	**Min**	**Max**	**Typ**
A	0.57	0.63	0.60
A1	0	0.05	0.03
A3	—	—	0.15
b	0.25	0.35	0.30
b1	0.185	0.285	0.235
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
E	1.95	2.05	2.00
E2	1.40	1.60	1.50
e	—	—	0.65
L	0.25	0.35	0.30
L1	0.82	0.92	0.87
K1	—	—	0.305
K2	—	—	0.225
Z	—	—	0.20
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.285
X2	1.050
Y	0.500
Y1	0.920
Y2	1.600
Y3	2.300

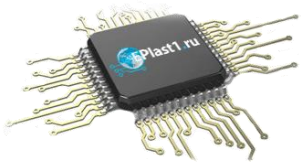
Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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